Please amend the application as follows:

IN THE CLAIMS:

Please amend claim 13 as follows:

Claim 13 (Amended). A method of CMP comprising:

forming a CMP slurry having a high structure polishing rate lower than a blanket polishing rate;

adding a slurry modifier to the slurry to produce a modified slurry that polishes high structures at a rate approximating the [blank] blanket polishing rate; and

polishing high structure areas.

Please add claims 17 through 20 as follows:

Claim 17 (New). A method of CMP comprising:

forming a CMP slurry having a low-density high structure polishing rate and a high-density high structure polishing rate, wherein the low-density high structure polishing rate is essentially the same as a high-density high structure polishing rate; and

polishing high structure areas, whereby the polishing rate is independent of pattern density.

Claim 18 (New). The method of claim 17, wherein said forming includes setting a cerium oxide concentration of between about 1% and 50% by weight.

Claim 19 (New). The method of claim 17, wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

Attachment to Preliminary Amendment Accompanying Continued Prosecution Application Under 37 § 1.53(d) Dated May 2, 2001

Claims Pending in Application Serial No. 09/270,606 Incorporating All Changes as of May 2, 2001

1. A method of CMP comprising:

forming a CMP slurry containing cerium oxide;

adding a slurry modifier to the slurry, wherein the slurry modifier polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure using the modifier-contained slurry.

2. The method of claim 1 wherein said forming includes setting a cerium oxide concentration of between about 1% and 50% by weight.

3. The method of claim 1 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

4. The method of claim 1 wherein said adding includes adding ethylene glycol at a concentration of up to 50%.

5. A method of CMP comprising:

forming a CMP slurry containing cerium oxide at a concentration of between about 1% and 50% by weight;

adding a slurry modifier to the slurry, wherein the slurry modifier polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure using the modifier-contained slurry.

6. The method of claim 5 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

7. The method of claim 5 wherein said adding includes adding ethylene glycol at a concentration of up to 50%.

8. A method of CMP comprising:

forming a CMP slurry containing cerium oxide at a concentration of between about 1% and 50% by weight;

adding ethylene glycol at a concentration of up to 50% for polishing low structure areas at a substantially zero rate and polishing high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure using the slurry.

9. The method of claim 8 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

10. A method of CMP comprising:

forming a CMP slurry containing cerium oxide;

adding a slurry modifier to the slurry to produce a modified slurry that polishes low structure areas at a substantially zero rate and polishes high structure areas at a rate approximating a blanket polishing rate; and

polishing a structure having high structure areas and low structure areas using the modified slurry, whereby high structure areas are polished at a rate approximating a blanket polishing rate and low structure areas are polished at a substantially zero rate.

11. The method of claim 10, wherein the high structure areas and the low structure areas are both formed of silicon dioxide.

12. The method of claim 10, wherein the slurry modifier is ethylene glycol.

13 (Amended). A method of CMP comprising:

forming a CMP slurry having a high structure polishing rate lower than a blanket polishing rate;

adding a slurry modifier to the slurry to produce a modified slurry that polishes high structures at a rate approximating the blanket polishing rate; and

polishing high structure areas.

14. The method of claim 13, wherein the CMP slurry comprises cerium oxide.

15. The method of claim 13, wherein the slurry modifier is ethylene glycol.

16. A method of chemically-mechanically polishing a silicon dioxide layer having high structure areas and low structure areas overlying a semiconductor substrate comprising:

forming a slurry comprising cerium oxide and ethylene glycol; and

polishing the silicon dioxide layer such that the high structure areas are polished at a rate approximating a blanket polishing rate, and the low structure areas are polished at a substantially zero rate.

Claim 17 (New). A method of CMP comprising:

forming a CMP slurry having a low-density high structure polishing rate and a high-density high structure polishing rate, wherein the low-density high structure polishing rate is essentially the same as a high-density high structure polishing rate; and

polishing high structure areas, whereby the polishing rate is independent of pattern density.

Claim 18 (New). The method of claim 17, wherein said forming includes setting a cerium oxide concentration of between about 1% and 50% by weight.

Claim 19 (New). The method of claim 17, wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

Claim 20 (New). The method of claim 17, wherein said forming includes adding ethylene glycol at a concentration of up to 50%.